54ACQ245, 74ACQ245, 54ACTQ245, 74ACTQ245

Quiet Series Octal Bidirectional Transceiver

The ‘ACQ/’ACTQ245 contains eight non-inverting bidirectional buffers with TRI-STATE outputs and is intended for bus-oriented applications. Current sinking capability is 24 mA at both the A and B ports. The Transmit/Receiver (T/R) input determines the direction of data flow through the bidirectional transceiver. Transmit (active-HIGH) enables data from A ports to B ports; Receive (active-LOW) enables data from B ports to A ports. The Output Enable input, when HIGH, disables both A and B ports by placing them in a HIGH Z condition.

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
    - Class Q Military
    - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
    - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer’s datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. ‘Typical’ values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

National Semiconductor

March 1993

54ACQ/74ACQ245 • 54ACTQ/74ACTQ245 Quiet Series Octal Bidirectional Transceiver with TRI-STATE® Inputs/Outputs

General Description

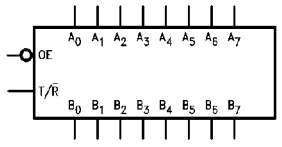
The 'ACQ/'ACTQ245 contains eight non-inverting bidirectional buffers with TRI-STATE outputs and is intended for bus-oriented applications. Current sinking capability is 24 mA at both the A and B ports. The Transmit/Receive (T/R) input determines the direction of data flow through the bidirectional transceiver. Transmit (active-HIGH) enables data from A ports to B ports; Receive (active-LOW) enables data from B ports to A ports. The Output Enable input, when HIGH, disables both A and B ports by placing them in a HIGH Z condition.

The 'ACQ/'ACTQ utilizes NSC Quiet Series technology to guarantee quiet output switching and improve dynamic threshold performance. FACT Quiet Series™ features GTO™ output control and undershoot corrector in addition to a split ground bus for superior performance.

Features

- I_{CC} and I_{OZ} reduced by 50%
- Guaranteed simultaneous switching noise level and dynamic threshold performance
- Guaranteed pin-to-pin skew AC performance
- Improved latch-up immunity
- TRI-STATE outputs drive bus lines or buffer memory address registers
- Outputs source/sink 24 mA
- Faster prop delays than the standard 'ACT245
- 4 kV minimum ESD immunity ('ACQ)
- Standard Military Drawing (SMD)
  - — 'ACTQ245: 5962-8766303
  - — 'ACQ245: 5962-92177

Logic Symbols



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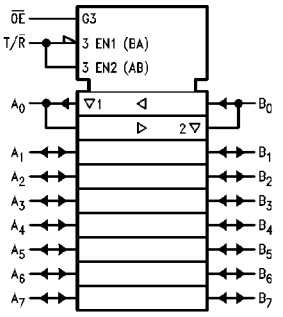
IEEE/IEC



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Pin Names	Description
$\overline{OE}$	Output Enable Input
T/$\overline{R}$	Transmit/Receive Input
A_0–A_7	Side A TRI-STATE Inputs or TRI-STATE Outputs
B_0–B_7	Side B TRI-STATE Inputs or TRI-STATE Outputs

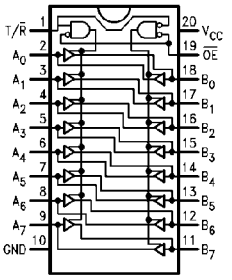
Truth Table

Inputs		Outputs
$\overline{OE}$	T/$\overline{R}$	
L	L	Bus B Data to Bus A
L	H	Bus A Data to Bus B
H	X	HIGH-Z State

H = HIGH Voltage Level
L = LOW Voltage Level
X = Immaterial

Connection Diagrams

Pin Assignment for DIP, Flatpak, QSOP and SOIC



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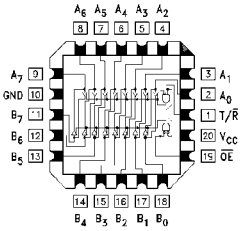
Pin Assignment for LCC



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RRD-B30M75/Printed in U. S. A.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5V to +7.0V
DC Input Diode Current (I_{IK})	
V_I = −0.5V	−20 mA
V_I = V_{CC} + 0.5V	+20 mA
DC Input Voltage (V_I)	−0.5V to V_{CC} + 0.5V
DC Output Diode Current (I_{OK})	
V_O = −0.5V	−20 mA
V_O = V_{CC} + 0.5V	+20 mA
DC Output Voltage (V_O)	−0.5V to V_{CC} + 0.5V
DC Output Source or Sink Current (I_O)	±50 mA
DC V_{CC} or Ground Current per Output Pin (I_{CC} or I_{GND})	±50 mA
Storage Temperature (T_{STG})	−65°C to +150°C
DC Latch-Up Source or Sink Current	±300 mA
Junction Temperature (T_J)	
CDIP	175°C
PDIP	140°C

Note 1: Absolute maximum ratings are those values beyond which damage to the device may occur. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. National does not recommend operation of FACT circuits outside databook specifications.

Recommended Operating Conditions

Supply Voltage (V_{CC})	
'ACQ	2.0V to 6.0V
'ACTQ	4.5V to 5.5V
Input Voltage (V_I)	0V to V_{CC}
Output Voltage (V_O)	0V to V_{CC}
Operating Temperature (T_A)	
74ACQ/ACTQ	−40°C to +85°C
54ACQ/ACTQ	−55°C to +125°C
Minimum Input Edge Rate ΔV/Δt 'ACQ Devices V_{IN} from 30% to 70% of V_{CC} V_{CC} @ 3.0V, 4.5V, 5.5V	125 mV/ ns
Minimum Input Edge Rate ΔV/Δt 'ACTQ Devices V_{IN} from 0.8V to 2.0V V_{CC} @ 4.5V, 5.5V	125 mV/ns

Note: All commercial packaging is not recommended for applications requiring greater than 2000 temperature cycles from −40°C to +125°C.

DC Characteristics for 'ACQ Family Devices

Symbol	Parameter	V_{CC} (V)	74ACQ		54ACQ	74ACQ	Units	Conditions
			T_A = +25°C		T_A = −55°C to +125°C	T_A = −40°C to +85°C		
			Typ	Guaranteed Limits				
V_{IH}	Minimum High Level Input Voltage	3.0	1.5	2.1	2.1	2.1	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
		4.5	2.25	3.15	3.15	3.15		
		5.5	2.75	3.85	3.85	3.85		
V_{IL}	Maximum Low Level Input Voltage	3.0	1.5	0.9	0.9	0.9	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
		4.5	2.25	1.35	1.35	1.35		
		5.5	2.75	1.65	1.65	1.65		
V_{OH}	Minimum High Level Output Voltage	3.0	2.99	2.9	2.9	2.9	V	I_{OUT} = −50 μA
		4.5	4.49	4.4	4.4	4.4		
		5.5	5.49	5.4	5.4	5.4		
		3.0		2.56	2.4	2.46	V	*V_{IN} = V_{IL} or V_{IH} I_{OH} −12 mA
		4.5		3.86	3.7	3.76		I_{OH} −24 mA
		5.5		4.86	4.7	4.76		−24 mA
V_{OL}	Maximum Low Level Output Voltage	3.0	0.002	0.1	0.1	0.1	V	I_{OUT} = 50 μA
		4.5	0.001	0.1	0.1	0.1		
		5.5	0.001	0.1	0.1	0.1		
		3.0		0.36	0.50	0.44	V	*V_{IN} = V_{IL} or V_{IH} I_{OL} 12 mA
		4.5		0.36	0.50	0.44		I_{OL} 24 mA
		5.5		0.36	0.50	0.44		24 mA
I_{IN}	Maximum Input Leakage Current	5.5		±0.1	±1.0	±1.0	μA	V_I = V_{CC}, GND (Note 1)

*All outputs loaded; thresholds on input associated with output under test.

DC Characteristics for 'ACQ Family Devices (Continued)

Symbol	Parameter	V_{CC} (V)	74ACQ $T_A = +25°C$		54ACQ $T_A = -55°C$ to $+125°C$	74ACQ $T_A = -40°C$ to $+85°C$	Units	Conditions
			Typ	Guaranteed Limits				
I_{OLD}	†Minimum Dynamic Output Current	5.5			50	75	mA	V_{OLD} = 1.65V Max
I_{OHD}		5.5			−50	−75	mA	V_{OHD} = 3.85V Min
I_{CC}	Maximum Quiescent Supply Current	5.5		4.0	80.0	40.0	μA	$V_{IN} = V_{CC}$ or GND (Note 1)
I_{OZT}	Maximum I/O Leakage Current	5.5		±0.3	±5.5	±3.0	μA	$V_I(OE) = V_{IL}, V_{IH}$ $V_I = V_{CC}$, GND $V_O = V_{CC}$, GND
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	5.0	1.1	1.5			V	*Figures 2-12, 13* (Notes 2, 3)
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	5.0	−0.6	−1.2			V	*Figures 2-12, 13* (Notes 2,3)
V_{IHD}	minimum High Level Dynamic Input Voltage	5.0	3.1	3.5			V	(Notes 2, 4)
V_{ILD}	Maximum Low Level Dynamic Input Voltage	5.0	1.9	1.5			V	(Notes 2, 4)

†Maximum test duration 2.0 ms, one output loaded at a time.

Note 1: I_{IN} and I_{CC} @ 3.0V are guaranteed to be less than or equal to the respective limit @ 5.5V V_{CC}. I_{CC} for 54ACQ @ 25°C is identical to 74ACQ @ 25°C.

Note 2: Plastic DIP package.

Note 3: Max number of outputs defined as (n). Data Inputs are driven 0V to 5V; one output @ GND.

Note 4: Max number of Data Inputs (n) switching. (n−1) Inputs switching 0V to 5V ('ACQ). Input-under-test switching: 5V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f = 1 MHz.

DC Characteristics for 'ACTQ Family Devices

Symbol	Parameter	V_{CC} (V)	74ACTQ $T_A = +25°C$		54ACTQ $T_A = -55°C$ to $+125°C$	74ACTQ $T_A = -40°C$ to $+85°C$	Units	Conditions
			Typ	Guaranteed Limits				
V_{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	2.0 2.0	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
V_{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	0.8 0.8	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
V_{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	4.4 5.4	V	I_{OUT} = −50 μA
		4.5 5.5		3.86 4.86	3.70 4.70	3.76 4.76	V	*$V_{IN} = V_{IL}$ or V_{IH} I_{OH} −24 mA I_{OH} −24 mA
V_{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	0.1 0.1	V	I_{OUT} = 50 μA
		4.5 5.5		0.36 0.36	0.50 0.50	0.44 0.44	V	*$V_{IN} = V_{IL}$ or V_{IH} I_{OL} 24 mA I_{OL} 24 mA
I_{IN}	Maximum Input Leakage Current	5.5		±0.1	±1.0	±1.0	μA	$V_I = V_{CC}$, GND

*All outputs loaded; thresholds on input associated with output under test.

DC Characteristics for 'ACTQ Family Devices (Continued)

Symbol	Parameter	V_{CC} (V)	74ACTQ $T_A = +25°C$	54ACTQ $T_A = -55°C$ to $+125°C$	74ACTQ $T_A = -40°C$ to $+85°C$	Units	Conditions
			Typ	Guaranteed Limits			
I_{OZT}	Maximum TRI-STATE Leakage Current	5.5		±0.3	±5.5	±3.0	μA	$V_I = V_{IL}, V_{IH}$ $V_O = V_{CC}$, GND
I_{CCT}	Maximum I_{CC}/Input	5.5	0.6		1.6	1.5	mA	$V_I = V_{CC} - 2.1V$
I_{OLD}	†Minimum Dynamic Output Current	5.5			50	75	mA	V_{OLD} = 1.65V Max
I_{OHD}		5.5			−50	−75	mA	V_{OHD} = 3.85V Min
I_{CC}	Maximum Quiescent Supply Current	5.5		4.0	80.0	40.0	μA	$V_{IN} = V_{CC}$ or GND (Note 1)
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	5.0	1.1	1.5			V	*Figures 2-12, 13* (Notes 2, 3)
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	5.0	−0.6	−1.2			V	*Figures 2-12, 13* (Notes 2, 3)
V_{IHD}	Minimum High Level Dynamic Input Voltage	5.0	1.9	2.2			V	(Notes 2, 4)
V_{ILD}	Maximum Low Level Dynamic Input Voltage	5.0	1.2	0.8			V	(Notes 2, 4)

†Maximum test duration 2.0 ms, one output loaded at a time.

Note 1: I_{CC} for 54ACTQ @ 25°C is identical to 74ACTQ @ 25°C.

Note 2: Plastic DIP package.

Note 3: Max number of outputs defined as (n). n−1 Data Inputs are driven 0V to 3V; one output @ GND.

Note 4: Max number of Data Inputs (n) switching. (n−1) Inputs switching 0V to 3V ('ACTQ). Input-under-test switching: 3V to threshold (V_{ILD}), 0V to threshold (V_{IHD}) f = 1 MHz.

AC Electrical Characteristics

Symbol	Parameter	V_{CC}* (V)	74ACQ $T_A = +25°C$, $C_L = 50$ pF			54ACQ $T_A = -55°C$ to $+125°C$, $C_L = 50$ pF		74ACQ $T_A = -40°C$ to $+85°C$, $C_L = 50$ pF		Units
			Min	Typ	Max	Min	Max	Min	Max	
t_{PHL}, t_{PLH}	Propagation Delay Data to Output	3.3	2.0	7.5	10.0	1.0	11.5	2.0	10.5	ns
		5.0	1.5	5.0	6.5	1.0	8.5	1.5	7.0	
t_{PZL}, t_{PZH}	Output Enable Time	3.3	3.0	8.5	13.0	1.0	13.0	3.0	13.5	ns
		5.0	2.0	6.0	8.5	1.0	10.0	2.0	9.0	
t_{PHZ}, t_{PLZ}	Output Disable Time	3.3	1.0	8.5	14.5	1.0	13.0	1.0	15.0	ns
		5.0	1.0	7.5	9.5	1.0	10.0	1.0	10.0	
t_{OSHL}, t_{OSLH}	Output to Output Skew** Data to Output	3.3		1.0	1.5				1.5	ns
		5.0		0.5	1.0				1.0	

*Voltage Range 5.0 is 5.0V ±0.5V
Voltage Range 3.3 is 3.3V ±0.3V

**Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH to LOW (t_{OSHL}) or LOW to HIGH (t_{OSLH}). Parameter guaranteed by design.

AC Electrical Characteristics

Symbol	Parameter	V_{CC}* (V)	74ACTQ $T_A = +25°C$, $C_L = 50$ pF			54ACTQ $T_A = -55°C$ to $+125°C$, $C_L = 50$ pF		74ACTQ $T_A = -40°C$ to $+85°C$, $C_L = 50$ pF		Units
			Min	Typ	Max	Min	Max	Min	Max	
t_{PHL}, t_{PLH}	Propagation Delay Data to Output	5.0	1.5	5.5	7.0	1.5	9.0	1.5	7.5	ns
t_{PZL}, t_{PZH}	Output Enable Time	5.0	2.0	7.0	9.0	1.5	12.0	2.0	9.5	ns
t_{PHZ}, t_{PLZ}	Output Disable Time	5.0	1.0	8.0	10.0	1.0	11.5	1.0	10.5	ns
t_{OSHL}, t_{OSLH}	Output to Output Skew** Data to Output	5.0		0.5	1.0				1.0	ns

*Voltage Range 5.0 is 5.0V ±0.5V

**Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH to LOW (t_{OSHL}) or LOW to HIGH (t_{OSLH}). Parameter guaranteed by design.

Capacitance

Symbol	Parameter	Typ	Units	Conditions
C_{IN}	Input Capacitance	4.5	pF	V_{CC} = OPEN
$C_{I/O}$	Input/Output Capacitance	15	pF	V_{CC} = 5.0V
C_{PD}	Power Dissipation Capacitance	80.0	pF	V_{CC} = 5.0V

FACT Noise Characteristics

The setup of a noise characteristics measurement is critical to the accuracy and repeatability of the tests. The following is a brief description of the setup used to measure the noise characteristics of FACT.

Equipment:

Hewlett Packard Model 8180A Word Generator
PC-163A Test Fixture
Tektronics Model 7854 Oscilloscope

Procedure:

1. Verify Test Fixture Loading: Standard Load 50 pF, 500Ω.
2. Deskew the word generator so that no two channels have greater than 150 ps skew between them. This requires that the oscilloscope be deskewed first. Swap out the channels that have more than 150 ps of skew until all channels being used are within 150 ps. It is important to deskew the word generator channels before testing. This will ensure that the outputs switch simultaneously.
3. Terminate all inputs and outputs to ensure proper loading of the outputs and that the input levels are at the correct voltage.
4. Set V_{CC} to 5.0V.
5. Set the word generator to toggle all but one output at a frequency of 1 MHz. Greater frequencies will increase DUT heating and affect the results of the measurement.

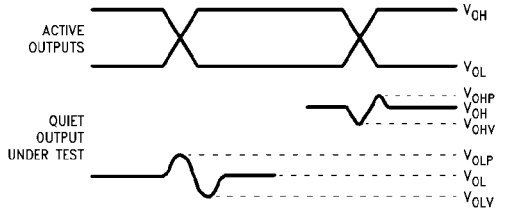


FIGURE 8. Quiet Output Noise Voltage Waveforms

Note A. V_{OHV} and V_{OLP} are measured with respect to ground reference.

Note B. Input pulses have the following characteristics: f = 1 MHz, t_r = 3 ns, t_f = 3 ns, skew < 150 ps.

6. Set the word generator input levels at 0V LOW and 3V HIGH for ACT devices and 0V LOW and 5V HIGH for AC devices. Verify levels with a digital volt meter.

V_{OLP}/V_{OLV} and V_{OHP}/V_{OHV}:

- Determine the quiet output pin that demonstrates the greatest noise levels. The worst case pin will usually be the furthest from the ground pin. Monitor the output voltages using a 50Ω coaxial cable plugged into a standard SMB type connector on the test fixture. Do not use an active FET probe.
- Measure V_{OLP} and V_{OLV} on the quiet output during the HL transition. Measure V_{OHP} and V_{OHV} on the quiet output during the LH transition.
- Verify that the GND reference recorded on the oscilloscope has not drifted to ensure the accuracy and repeatability of the measurements.

V_{ILD} and V_{IHD}:

- Monitor one of the switching outputs using a 50Ω coaxial cable plugged into a standard SMB type connector on the test fixture. Do not use an active FET probe.
- First increase the input LOW voltage level, V_{IL}, until the output begins to oscillate. Oscillation is defined as noise on the output LOW level that exceeds V_{IL} limits, or on output HIGH levels that exceed V_{IH} limits. The input LOW voltage level at which oscillation occurs is defined as V_{ILD}.
- Next increase the input HIGH voltage level on the word generator, V_{IH} until the output begins to oscillate. Oscillation is defined as noise on the output LOW level that exceeds V_{IL} limits, or on output HIGH levels that exceed V_{IH} limits. The input HIGH voltage level at which oscillation occurs is defined as V_{IHD}.
- Verify that the GND reference recorded on the oscilloscope has not drifted to ensure the accuracy and repeatability of the measurements.

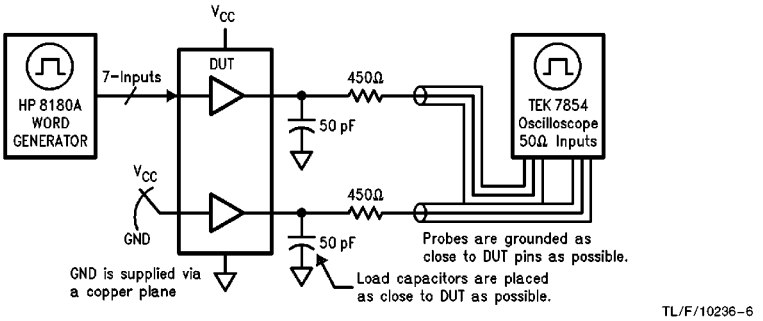


FIGURE 9. Simultaneous Switching Test Circuit

Ordering Information

The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

74ACTQ 245 P C QR

Temperature Range Family
- 74ACQ = Commercial
- 54ACQ = Military
- 74ACTQ = Commercial TTL-Compatible
- 54ACTQ = Military TTL-Compatible

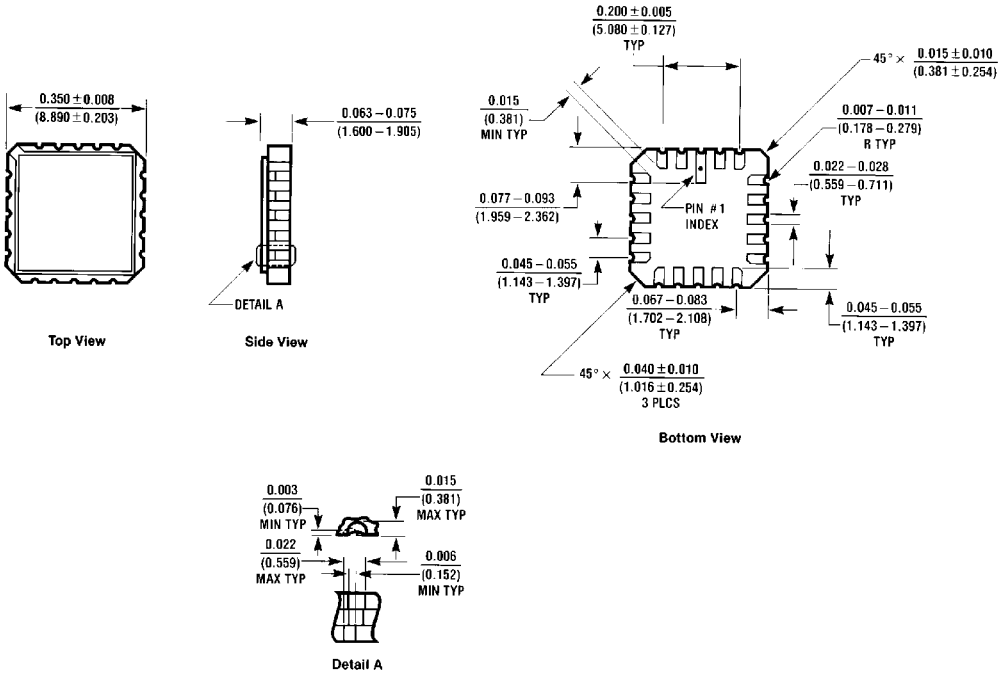
Device Type

Package Code
- P = Plastic DIP
- D = Ceramic DIP
- F = Flatpak
- L = Leadless Ceramic Chip Carrier (LCC)
- S = Small Outline Package (SOIC)
- QS = Quarter Size Outline Package (QSOP)

Special Variations
- X = Device shipped in 13" reels
- QR = Commercial grade device with burn-in
- QB = Military grade device with environmental and burn-in processing shipped in tubes

Temperature Range
- C = Commercial (−40°C to +85°C)
- M = Military (−55°C to +125°C)

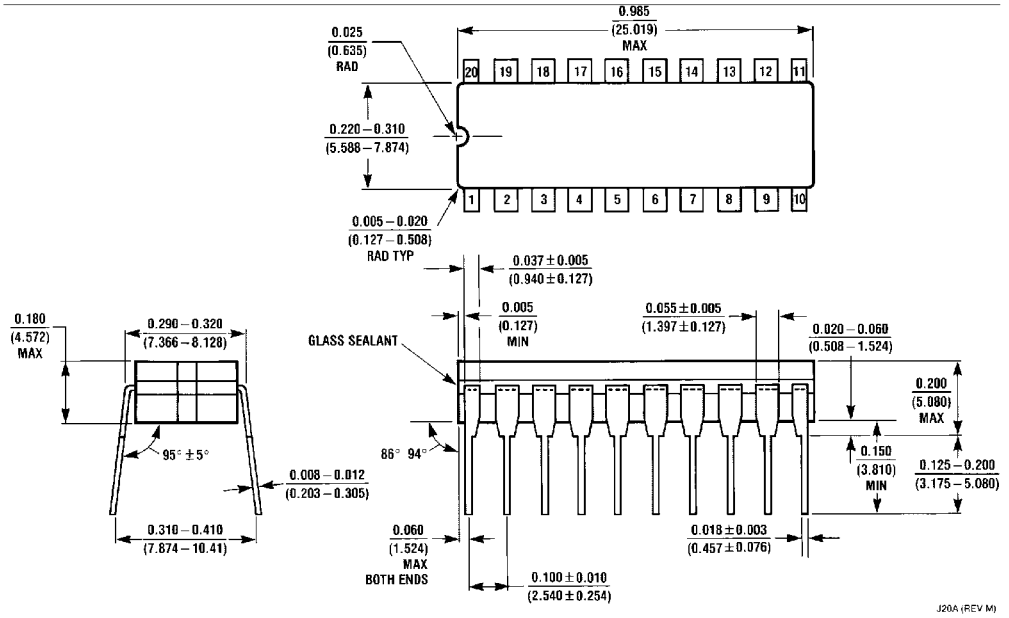
Physical Dimensions inches (millimeters)



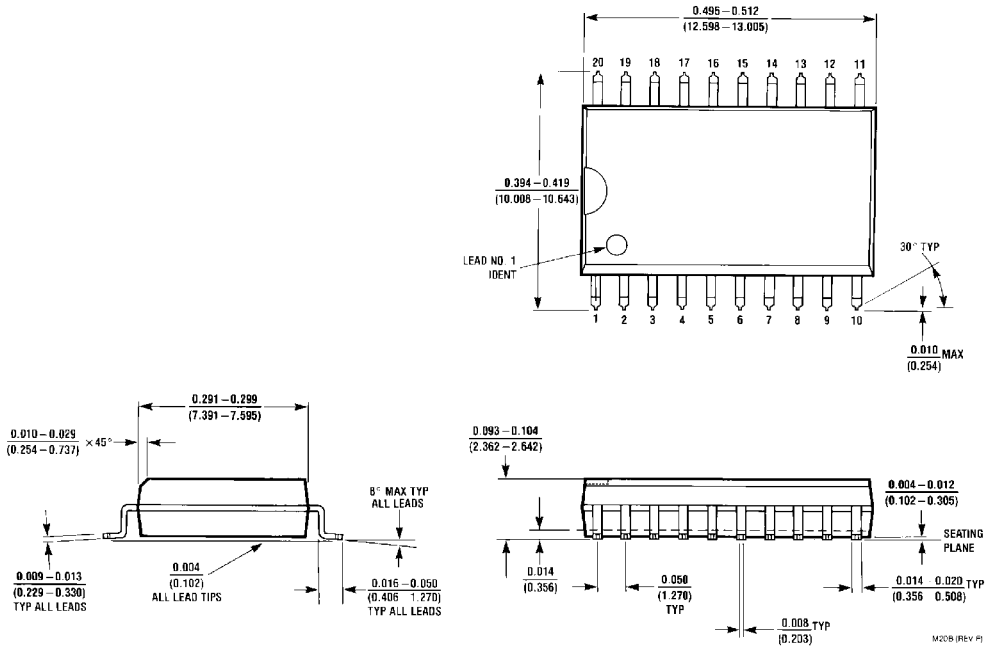
E20A (REV D)

20-Terminal Ceramic Leadless Chip Carrier (L)
NS Package Number E20A

Physical Dimensions inches (millimeters) (Continued)

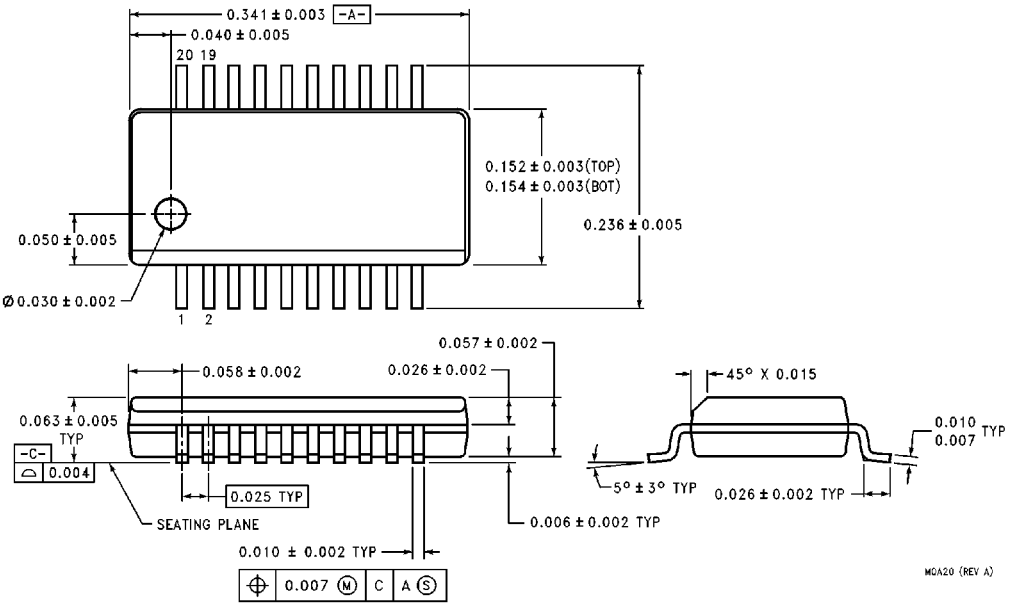


20-Lead Ceramic Dual-In-Line Package (D)
NS Package Number J20A

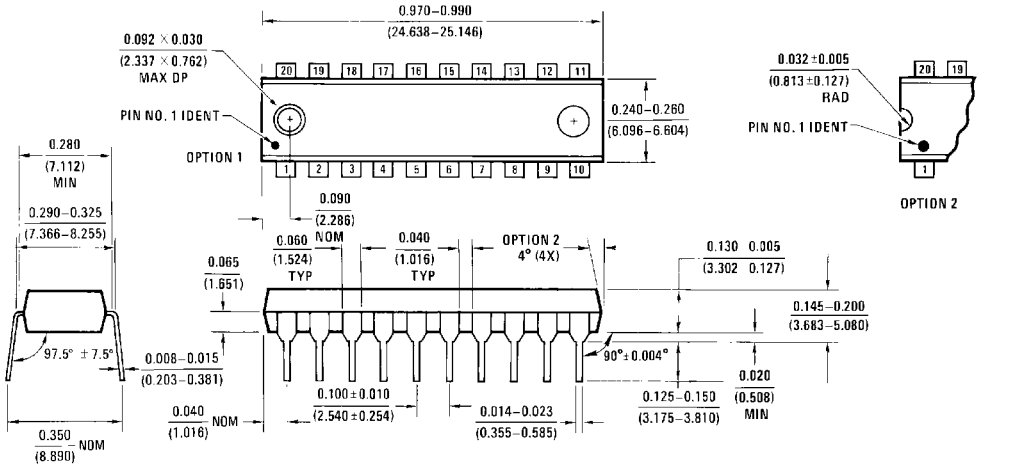


20-Lead Small Outline Integrated Circuit (S)
NS Package Number M20B

Physical Dimensions inches (millimeters) (Continued)



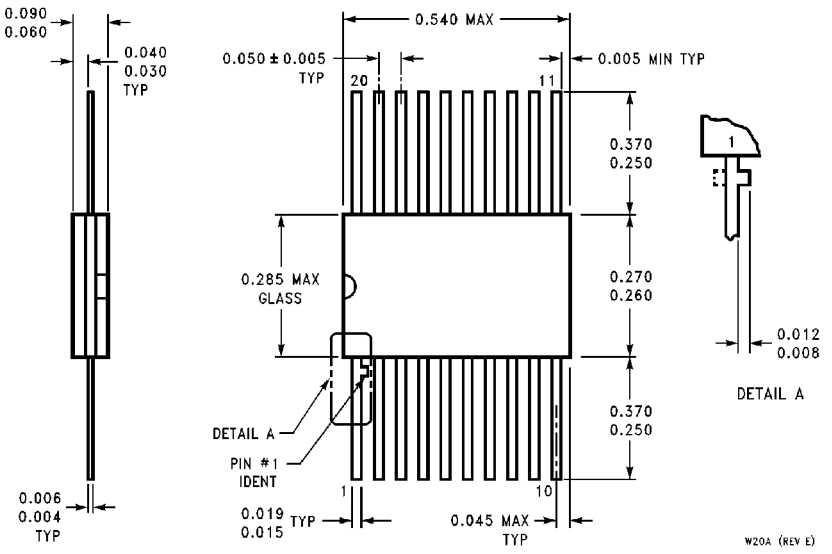
20-Lead Quarter Size Outline Package (QS)
NS Package Number MQA20



20-Lead Plastic Dual-In-Line Package (P)
NS Package Number N20B

Physical Dimensions inches (millimeters) (Continued)

Lit. # 114675



20-Lead Ceramic Flatpak (F)
NS Package Number W20A

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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